Dual Bias Resistor Transistors

NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

EMD5DXV6T5G

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the EMD5DXV6 series, two complementary BRT devices are housed in the SOT-563 package which is ideal for low power surface mount applications where board space is at a premium.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch Tape and Reel
- Lead Free Solder Plating
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted, common for Q_1 and Q_2 , – minus sign for Q_1 (PNP) omitted)

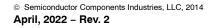
Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	Ι _C	100	mAdc

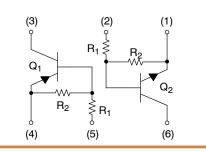
THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	357 (Note 1) 2.9 (Note 1)	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	350 (Note 1)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	500 (Note 1) 4.0 (Note 1)	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ hetaJA}$	250 (Note 1)	°C/W
Junction and Storage Temperature	T _J , T _{stg}	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.









SOT-563 CASE 463A

MARKING DIAGRAM



- U5 = Specific Device Code
- M = Month Code
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
EMD5DXV6T5G	SOT-563 (Pb-Free)	8000 / Tape & Reel
EMD5DXV6T1G	SOT–563 (Pb–Free)	4000 / Tape & Reel

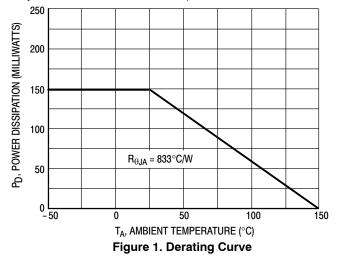
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

EMD5DXV6T5G

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

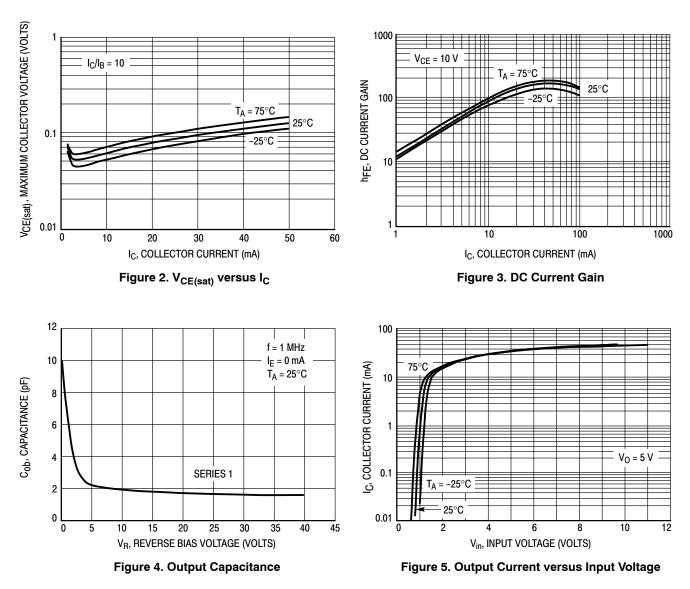
Characteristic	Symbol	Min	Тур	Мах	Unit
Q1 TRANSISTOR: PNP					
OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V _{CB} = 50 V, $I_E = 0$)	I _{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current (V_{CB} = 50 V, I_B = 0)	I _{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0, I_{C} = 5.0 mA)	I _{EBO}	-	-	1.0	mAdc
ON CHARACTERISTICS					
Collector-Base Breakdown Voltage (I _C = 10 μ A, I _E = 0)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (I_{C} = 2.0 mA, I_{B} = 0)	V _{(BR)CEO}	50	-	-	Vdc
DC Current Gain (V_{CE} = 10 V, I _C = 5.0 mA)	h _{FE}	20	35	-	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA)	V _{CE(SAT)}	-	-	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 k\Omega)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 k\Omega)	V _{OH}	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R1/R2	0.38	0.47	0.56	
Q2 TRANSISTOR: NPN					
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50 \text{ V}, I_E = 0$)	I _{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current (V_{CB} = 50 V, I_B = 0)	I _{CEO}	_	-	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0, I_{C} = 5.0 mA)	I _{EBO}	-	-	0.1	mAdc
ON CHARACTERISTICS					
Collector-Base Breakdown Voltage ($I_C = 10 \ \mu A$, $I_E = 0$)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 2.0 \text{ mA}, I_B = 0$)	V _{(BR)CEO}	50	-	_	Vdc
DC Current Gain (V _{CE} = 10 V, I_C = 5.0 mA)	h _{FE}	80	140	-	1
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$)	V _{CE(SAT)}	-	-	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 k\Omega)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 k Ω)	V _{OH}	4.9	-	-	Vdc
Input Resistor	R1	33	47	61	kΩ
Resistor Ratio	R1/R2	0.8	1.0	1.2	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



EMD5DXV6T5G

TYPICAL ELECTRICAL CHARACTERISTICS — EMD5DXV6 PNP TRANSISTOR



EMD5DXV6T5G

TYPICAL ELECTRICAL CHARACTERISTICS — EMD5DXV6 NPN TRANSISTOR

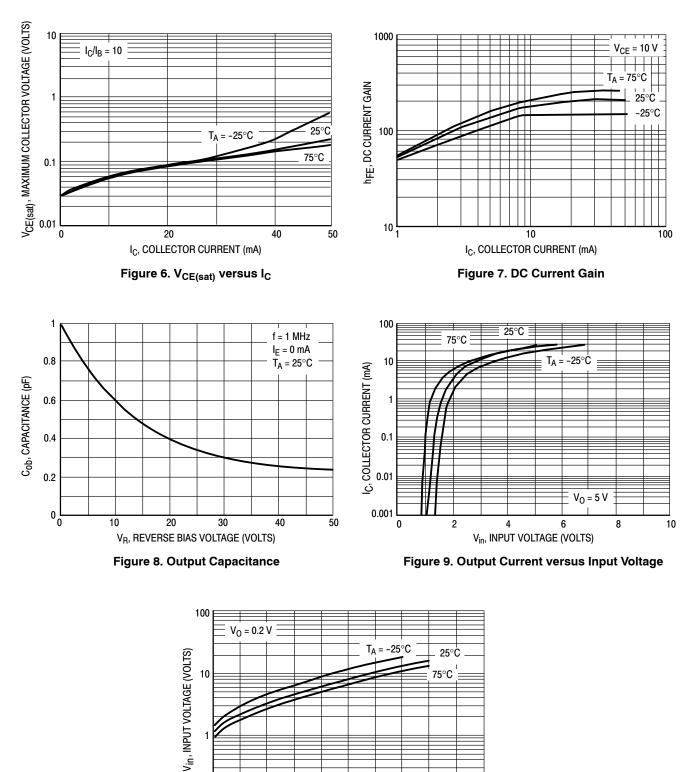


Figure 10. Input Voltage versus Output Current

I_C, COLLECTOR CURRENT (mA)

30

40

50

20

0.1 L 0

10

6Х

(

MILLIMETERS

NDM.

0.55

0.22

0.13

1.60

1.20

0.50 BSC

0.20

1.60

MAX.

0.60

0.27

0.18

1.70

1.30

0.30

1.70

SIDE VIEW

MIN.

0.50

0.17

0.08

1.50

1.10

0.10

1.50

DIM

Α

b

С

D E

e L

 H_E



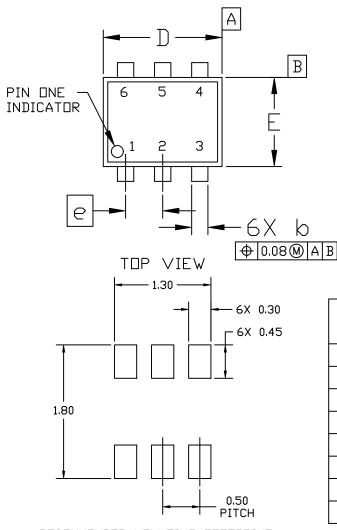


SOT-563, 6 LEAD CASE 463A ISSUE H

DATE 26 JAN 2021

ALE 4:1

- NDTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 1. DIMENSIONING AND TOLERANCING PER A 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF BASE MATERIAL.



RECOMMENDED MOUNTING FOOTPRINT* * For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

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STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHIDE 1
2. BASE 1	2. EMITTER 2	2. CATHIDE 1
3. COLLECTOR 2	3. BASE 2	3. ANUDE/ANUDE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHIDE 2
5. BASE 2	5. BASE 1	5. CATHIDE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. ANUDE/ANUDE 1
STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. COLLECTOR	PIN 1. CATHEDE	PIN 1. CATHODE
2. COLLECTOR	2. CATHEDE	2. ANODE
3. BASE	3. ANEDE	3. CATHODE
4. EMITTER	4. ANEDE	4. CATHODE
5. COLLECTOR	5. CATHEDE	5. CATHODE
6. COLLECTOR	6. CATHEDE	6. CATHODE
STYLE 7:	STYLE 8:	STYLE 9:
PIN 1. CATHODE	PIN 1. DRAIN	PIN 1. SDURCE 1
2. ANODE	2. DRAIN	2. GATE 1
3. CATHODE	3. GATE	3. DRAIN 2
4. CATHODE	4. SDURCE	4. SDURCE 2
5. ANODE	5. DRAIN	5. GATE 2
6. CATHODE	6. DRAIN	6. DRAIN 1
STYLE 10: PIN 1. CATHIDE 1 2. N/C 3. CATHIDE 2 4. ANIDE 2 5. N/C 6. ANIDE 1	STYLE 11: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	

6. COLLECTOR 2

DATE 26 JAN 2021

GENERIC **MARKING DIAGRAM***



XX = Specific Device Code

M = Month Code

. = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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